

INCHANGE SEMICONDUCTOR

isc N-Channel Mosfet Transistor

BUZ76A

FEATURES

- 2.6A, 400V
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Designed for switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power.

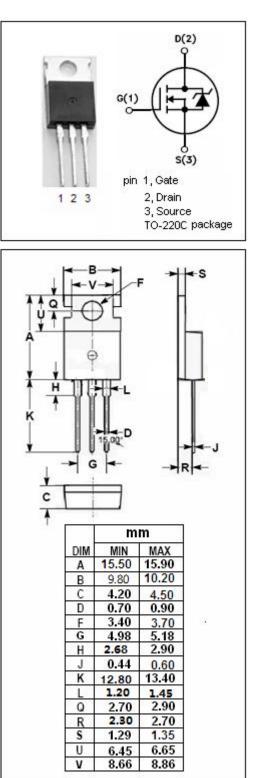
| SYMBOL | ARAMETER | VALUE | UNIT |
|------------------|---|---------|------|
| V _{DSS} | Drain-Source Voltage (V _{GS} =0) | 400 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| ID | Drain Current-continuous@ TC=30°C | 2.6 | A |
| I _{DM} | Drain Current-Single Plused | 10 | А |
| P _{tot} | Total Dissipation@TC=25°C | 40 | W |
| Tj | Max. Operating Junction Temperature 150 | | °C |
| T _{stg} | Storage Temperature Range | -55~150 | °C |

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|---------------------|---|-----|------|
| Rth j-c | Thermal Resistance, Junction to Case | 3.1 | °C/W |
| R _{th j-a} | Thermal Resistance, Junction to Ambient | 75 | °C/W |

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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|----------------------|---------------------------------|--|-----|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D =0.25mA | 400 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V_{DS} = V_{GS} ; I_D =1mA | 2.1 | | 4.0 | V |
| V _{SD} | Diode Forward On-voltage | I _S = 5.2A ;V _{GS} = 0 | | | 1.4 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 1.5A | | | 2.5 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±20V;V _{DS} = 0 | | | ±100 | nA |
| IDSS | Zero Gate Voltage Drain Current | V _{DS} =400V; V _{GS} = 0 | | | 1 | μA |
| Gfs | Forward Transconductance | V _{DS} = 25V; I _D =1.5A | 2.1 | | | S |
| t _{d(on)} | Turn-on Delay Time | V _{GS} =10V; | | | 20 | |
| tr | Rise Time | I _D =2.4A; | | | 60 | |
| $t_{d(off)}$ | Turn-off Delay Time | V _{DD} =30V; R _{GS} =50 Ω | | | 65 | ns |
| t _f | Fall Time | | | | 40 | |

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